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8-bit Shift Register/Latch (with 3-state outputs)



ADE-205-514 (Z) 1st. Edition Sep. 2000

Description

This device each contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. The storage register has parallel 3-state outputs. Separate clocks are provided for both the shift register and the storage register. The shift register has a direct-overriding clear, serial input, and serial output pins for cascading.

Both the shift register and storage register clocks are positive-edge triggered. If the user wishes to connect both clocks together, the shift register state will always be one clock pulse ahead of the storage register.

Features

• High Speed Operation: t_{pd} (RCK to Q) = 17 ns typ ($C_L = 50 \text{ pF}$)

High Output Current: Fanout of 15 LSTTL Loads (Q_A to Q_H outputs)

• Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$

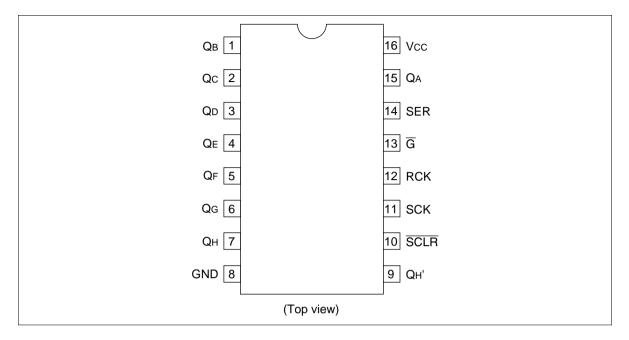
• Low Input Current: 1 µA max

• Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max (Ta = 25°C)

Function Table

RCK	SCK	SCLR	G	Function
X	Χ	Х	Н	$\mathbf{Q}_{_{\mathrm{A}}}$ to $\mathbf{Q}_{_{\mathrm{H}}}$ high impedance
X	Х	L	Χ	Shift register cleared Q _H ' = L
X	\int	Н	X	Shift register clocked $Q_n = Q_{n-1}$, $Q_A = SER$
\int	Χ	Н	Χ	Contents of shift register transferred to output latches

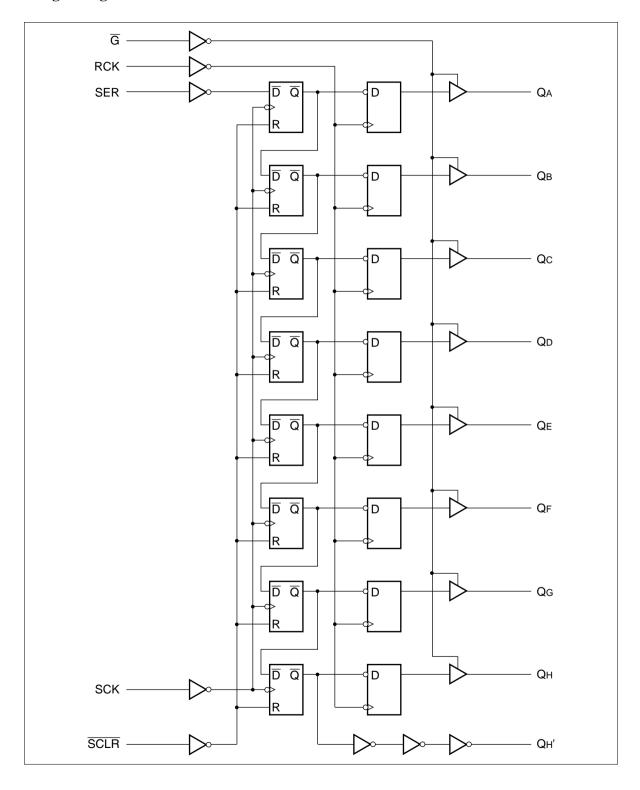
Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Rating	Unit	
Supply voltage range	V _{cc}	-0.5 to +7.0	V	
Input voltage	V _{IN}	-0.5 to $V_{cc} + 0.5$	V	
Output voltage	V _{OUT}	-0.5 to $V_{cc} + 0.5$	V	
Output current	I _{OUT}	±35	mA	
DC current drain per V _{cc} , GND	I _{CC} , I _{GND}	±75	mA	
DC input diode current	I _{IK}	±20	mA	
DC output diode current	I _{ok}	±20	mA	
Power dissipation per package	P _T	500	mW	
Storage Temperature	Tstg	-65 to +150	°C	

Logic Diagram



DC Characteristics

			Ta =	: 25°C	;	Ta = - +85°C	-40 to			
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Min	Max	Unit	Test Condition	ns
Input voltage	V _{IH}	2.0	1.5	_	_	1.5	_	V		
		4.5	3.15	_	_	3.15	_	_		
		6.0	4.2	_	_	4.2	_	=		
	V _{IL}	2.0	_	_	0.5	_	0.5	V		
		4.5	_	_	1.35	_	1.35	_		
		6.0	_	_	1.8	_	1.8	_		
Output voltage	V_{OH}	2.0	1.9	2.0	_	1.9	_	V	Q _A to Q _H	$I_{OH} = -20 \mu A$
		4.5	4.4	4.5	_	4.4	_	=	$Vin = V_{IH} \text{ or } V_{IL}$	
		6.0	5.9	6.0	_	5.9	_	-		
		4.5	4.18	_	_	4.13	_	-		$I_{OH} = -6 \text{ mA}$
		6.0	5.68	_	_	5.63	_	=		$I_{OH} = -7.8 \text{ mA}$
	V _{OL}	2.0	_	0.0	0.1	_	0.1	V	Q _A to Q _H	I _{OL} = 20 μA
		4.5	_	0.0	0.1	_	0.1	=	$Vin = V_{IH} \text{ or } V_{IL}$	
		6.0	_	0.0	0.1	_	0.1	-		
		4.5	_	_	0.26	_	0.33	-		I _{OL} = 6 mA
		6.0	_	_	0.26	_	0.33	_		I _{OL} = 7.8 mA
Output voltage	V _{OH}	2.0	1.9	2.0	_	1.9	_	V	Q' _H	$I_{OH} = -20 \mu A$
		4.5	4.4	4.5	_	4.4	_	=	$Vin = V_{IH} \text{ or } V_{IL}$	
		6.0	5.9	6.0	_	5.9	_	=		
		4.5	4.18	_	_	4.13	_	-		$I_{OH} = -4 \text{ mA}$
		6.0	5.68	_	_	5.63	_	-		$I_{OH} = -5.2 \text{ mA}$
	V _{OL}	2.0	_	0.0	0.1	_	0.1	V	Q' _H	I _{OL} = 20 μA
		4.5	_	0.0	0.1	_	0.1	=	$Vin = V_{IH} \text{ or } V_{IL}$	
		6.0	_	0.0	0.1	_	0.1	=		
		4.5	_	_	0.26	_	0.33	-		I _{OL} = 4 mA
		6.0	_	_	0.26	_	0.33	-		I _{OL} = 5.2 mA
Off-state output current	l _{oz}	6.0	_	_	±0.5	_	±5.0	μΑ	$Vin = V_{IH} \text{ or } V_{IL}$ $Vout = V_{CC} \text{ or } C$	
Input current	lin	6.0	_	_	±0.1	_	±1.0	μΑ	Vin = V _{CC} or Gf	ND
Quiescent supply current	I _{cc}	6.0	_	_	4.0	_	40	μΑ	Vin = V _{cc} or Gf	ND, lout = 0 μA

AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Ta = -40 to Ta = 25°C +85°C

Item	Symbol	V_{cc} (V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Maximum clock	f _{max}	2.0	_	_	5	_	4	MHz	
frequency		4.5	_	_	27	_	21	_	
		6.0	_	_	31	_	24	=	
Propagation delay	t _{PLH}	2.0	_	_	115	_	145	ns	SCK to Q _H '
time	$t_{\tiny PHL}$	4.5	_	12	23	_	29	=	
		6.0	_	_	20	_	25	=	
	t _{PLH}	2.0	_	_	150	_	190	ns	RCK to Q
	$t_{\tiny PHL}$	4.5	_	17	30	_	38	=	
		6.0	_	_	26	_	33	=	
	t _{PLH}	2.0	_	_	175	_	220	ns	SCLR to Q _H '
		4.5	_	20	35	_	44	=	
		6.0	_	_	30	_	37	=	
Output enable	t _{zL}	2.0	_	_	150	_	190	ns	
time	t_{zH}	4.5	_	13	30	_	38	=	
		6.0	_	_	26	_	33	=	
Output disable	t _{LZ}	2.0	_	_	150	_	190	ns	
time	t_{HZ}	4.5	_	15	30	_	38	_	
		6.0	_	_	26	_	33	=	
Setup time	t _{su}	2.0	100	_	_	125	_	ns	SER to SCK
		4.5	20	1	_	25	_	_	
		6.0	17	_	_	21	_	_	
		2.0	200	_	_	250	_	ns	SCK to RCK
		4.5	40	8	_	50	_	=	
		6.0	34	_	_	43	_	-	
Pulse width	t _w	2.0	80	_	_	100	_	ns	
		4.5	16	8	_	20	_	-	
		6.0	14	_	_	17	_	_	
Removal time	t _{rem}	2.0	100	_	_	125	_	ns	
		4.5	20	_	_	25	_	_	
		6.0	17	_	_	21	_	=	

Input capacitance

AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$) (cont)

6.0

Cin

Ta = -40 toTa = 25°C +85°C V_{cc} (V) Min Typ Max Min Item Symbol Max Unit **Test Conditions** Hold time t_h 2.0 5 5 ns 4.5 5 1 5 6.0 5 5 Q_{H} Output rise/fall 2.0 75 $\mathbf{t}_{\mathsf{TLH}}$ 95 ns time 19 4.5 5 15 t_{THL} 6.0 13 16 2.0 60 75 ns Q 4.5 12 15 4

10

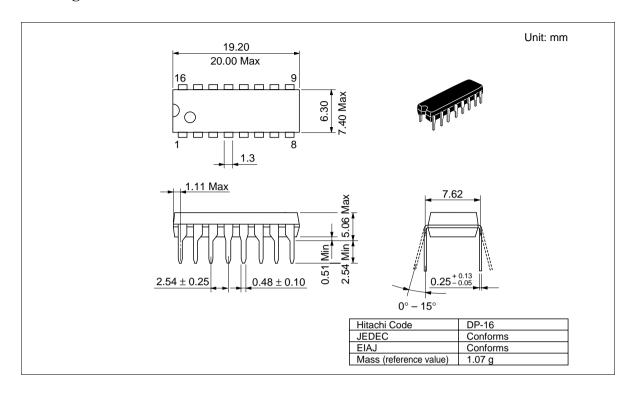
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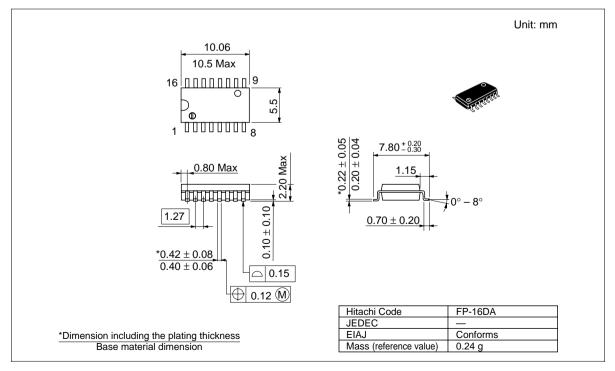
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13 5

рF

Package Dimensions





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